

L Number	Hits	Search Text	DB	Time stamp
1	66	438/288.cc1s.	USPAT	2004/03/11 10:47
2	906	438/585.cc1s. 438/591.cc1s.	USPAT	2004/03/11 10:47
3	963	(438/585.cc1s. 438/591.cc1s.) 438/288.cc1s.	USPAT	2004/03/11 10:47
-	20394	gate adj2 insulating	USPAT; EPO; JPO	2002/10/29 16:07
-	19039	thin adj2 oxide) (ultrathin adj2 oxide	USPAT; EPO; JPO	2002/10/29 16:07
-	1124	(gate adj2 insulating) and (thin adj2 oxide) (ultrathin adj2 oxide) and polysilicon	USPAT; EPO; JPO	2002/10/29 16:08
-	188199	hydrogen and oxygen	USPAT; EPO; JPO	2002/10/29 16:08
-	227	(hydrogen and oxygen) and ((gate adj2 insulating) and (thin adj2 oxide) (ultrathin adj2 oxide) and polysilicon)	USPAT; EPO; JPO	2002/10/29 16:08
-	101606	hydrogen same oxygen	USPAT; EPO; JPO	2002/10/29 16:09
-	122	(hydrogen same oxygen) and ((gate adj2 insulating) and (thin adj2 oxide) (ultrathin adj2 oxide) and polysilicon)	USPAT; EPO; JPO	2002/10/29 16:13
-	80371	hydrogen with oxygen	USPAT; EPO; JPO	2002/10/29 16:14
-	88	(hydrogen with oxygen) and ((gate adj2 insulating) and (thin adj2 oxide) (ultrathin adj2 oxide) and polysilicon)	USPAT; EPO; JPO	2002/10/30 10:11
-	1	(hydrogen with oxygen) and ((gate adj2 insulating) and (thin adj2 oxide) (ultrathin adj2 oxide) and polysilicon) and ISSG	USPAT; EPO; JPO	2002/10/30 10:16
-	9	ISSG "in situ steam generation"	USPAT; EPO; JPO	2004/02/26 13:44
-	8	(ISSG "in situ steam generation") and gate	USPAT; EPO; JPO	2002/10/30 10:31

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-	5957	EEPROM and oxide	USPAT; EPO; JPO	2003/04/27 14:47
-	54	(EEPROM and oxide) and SONOS	USPAT; EPO; JPO	2003/04/27 14:49
-	280	EEPROM and ("form oxide")	USPAT; EPO; JPO	2003/04/27 14:52
-	0	EEPROM and ("form oxide") near (oxygen adj3 hydrogen)	USPAT; EPO; JPO	2003/04/27 14:52
-	1	("form oxide") near (oxygen adj3 hydrogen)	USPAT; EPO; JPO	2003/04/27 14:53
-	184	("wet oxidation" or "steam oxidation") and EEPROM	USPAT; EPO; JPO	2003/04/27 15:00
-	16	("wet oxidation" or "steam oxidation") and EEPROM and (ultrathin "ultra-thin")	USPAT; EPO; JPO	2003/04/27 15:01
-	1694	((hydrogen or "H.Sub.2") near "3" (oxygen or "O.sub.2") or (pyrogenic pyrogenically pyrogenic wet steam)) near12 (oxidiz\$3 oxidis\$3 oxidation anneal\$4 RTO) near12 (SiN("Si.sub.3" adj "N.sub.4") Si3N4 nitride)	USPAT; EPO; JPO	2003/04/28 12:36
-	0	((((hydrogen or "H.Sub.2") near "3" (oxygen or "O.sub.2") or (pyrogenic pyrogenically pyrogenic wet steam)) near12 (oxidiz\$3 oxidis\$3 oxidation anneal\$4 RTO) near12 (SiN("Si.sub.3" adj "N.sub.4") Si3N4 nitride)) and "ultrathin oxide")	USPAT; EPO; JPO	2003/04/28 12:37
-	6	((((hydrogen or "H.Sub.2") near "3" (oxygen or "O.sub.2") or (pyrogenic pyrogenically pyrogenic wet steam)) near12 (oxidiz\$3 oxidis\$3 oxidation anneal\$4 RTO) near12 (SiN("Si.sub.3" adj "N.sub.4") Si3N4 nitride)) and (ultrathin near3 oxide))	USPAT; EPO; JPO	2003/04/28 12:48
-	26	((((hydrogen or "H.Sub.2") near "3" (oxygen or "O.sub.2") or (pyrogenic pyrogenically pyrogenic wet steam)) near12 (oxidiz\$3 oxidis\$3 oxidation anneal\$4 RTO) near12 (SiN("Si.sub.3" adj "N.sub.4") Si3N4 nitride)) and gardner.inv.	USPAT; EPO; JPO	2003/04/28 12:55
-	23	reoxidize near6 nitrogen	USPAT; EPO; JPO	2003/04/28 12:56
-	99	((((hydrogen or "H.Sub.2") near "3" (oxygen or "O.sub.2") or (pyrogenic pyrogenically pyrogenic wet steam)) near12 (oxidiz\$3 oxidis\$3 oxidation anneal\$4 RTO) near12 (SiN("Si.sub.3" adj "N.sub.4") Si3N4 nitride)) and EEPROM (RTO "rapid thermal oxidation") near5 minute	USPAT; EPO; JPO	2003/04/28 13:28
-	2	"tunnel oxide".clm.	USPAT; EPO; JPO	2003/04/28 13:28
-	690		USPAT; EPO; JPO	2004/02/26 13:45